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December 2014

FCP150N65F

N-Channel SuperFET® II FRFET® MOSFET

650 V, 24 A, 150 mΩ

Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 133 m Ω
- Ultra Low Gate Charge (Typ. Q_g = 72 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 361 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

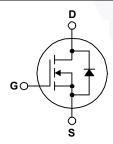
Applications

- LCD / LED / PDP TV Telecom / Server Power Supplies
- Solar Inverter
- · AC DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET II FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | | Parameter | | | |
|-----------------------------------|--------------------------------------|---|------------|------|------|
| V_{DSS} | Drain to Source Voltage | | | 650 | V |
| V | Cata ta Sauraa Valtaga | - DC | | ±20 | V |
| V _{GSS} | Gate to Source Voltage | - AC | (f > 1 Hz) | ±30 | v |
| In Drain Current | - Continuous (T _C = 25°C) | | 24 | Α | |
| ID | Drain Current | - Continuous (T _C = 100°C) | | 14.9 | _ A |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | 72 | Α |
| E _{AS} | Single Pulsed Avalanche Energy | Single Pulsed Avalanche Energy (Note 2) | | | mJ |
| I _{AR} | Avalanche Current | | (Note 1) | 4.7 | Α |
| E _{AR} | Repetitive Avalanche Energy | | (Note 1) | 2.98 | mJ |
| dv/dt | MOSFET dv/dt | | | 100 | Mag |
| dv/dt | Peak Diode Recovery dv/dt | | (Note 3) | 50 | V/ns |
| D | Dower Dissipation | (T _C = 25°C) | | 298 | W |
| P_{D} | Power Dissipation | - Derate Above 25°C | | 2.38 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperat | Operating and Storage Temperature Range | | | °C |
| TL | Maximum Lead Temperature for | Soldering, 1/8" from Case for 5 So | econds | 300 | °C |

Thermal Characteristics

| Symbol | Parameter FCP150N65F | | |
|-----------------|--|------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 0.42 | °C/W |
| $R_{	heta JA}$ | Thermal Resistance, Junction to Ambient, Max. 62.5 | | *C/VV |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|------------|---------|----------------|-----------|------------|----------|
| FCP150N65F | FCP150N65F | TO-220 | Tube | N/A | N/A | 50 units |

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|---|---|---|------|------|------|------|
| Off Charac | cteristics | | | | | |
| D\/ | Drain to Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 25^{\circ}\text{C}$ | 650 | - | - | V |
| BV _{DSS} | Diaili to Source Breakdowii Voltage | $V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 150^{\circ}\text{C}$ | 700 | - | - | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 10 mA, Referenced to 25°C | - | 0.72 | - | V/°C |
| I | Zero Gate Voltage Drain Current | V _{DS} = 650 V, V _{GS} = 0 V | - | - | 10 | |
| IDSS | Zero Gate Voltage Drain Current | $V_{DS} = 520 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$ | - | 86 | - | μА |
| I _{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | - | - | ±100 | nA |

On Characteristics

| V _{GS(th)} | Gate Threshold Voltage | $V_{GS} = V_{DS}$, $I_D = 2.4$ mA | 3 | - | 5 | V |
|---------------------|--------------------------------------|---|---|-----|-----|----|
| R _{DS(on)} | Static Drain to Source On Resistance | $V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$ | - | 133 | 150 | mΩ |
| 9 _{FS} | Forward Transconductance | V _{DS} = 20 V, I _D = 12 A | - | 22 | - | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz | | 2810 | 3737 | pF |
|---------------------|-------------------------------|---|---|------|------|----|
| C _{oss} | Output Capacitance | | | 91 | 121 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 0.77 | - | pF |
| C _{oss} | Output Capacitance | $V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | - | 54 | - | pF |
| Coss eff. | Effective Output Capacitance | V _{DS} = 0 V to 400 V, V _{GS} = 0 V | - | 361 | - | pF |
| Q _{g(tot)} | Total Gate Charge at 10V | V _{DS} = 380 V, I _D = 12 A, | | 72 | 94 | nC |
| Q_{gs} | Gate to Source Gate Charge | V _{GS} = 10 V | - | 15 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | (Note 4) | - | 31 | - | nC |
| ESR | Equivalent Series Resistance | f = 1 MHz | - | 0.69 | - | Ω |

Switching Characteristics

| t _{d(on)} | Turn-On Delay Time | V _{DD} = 380 V, I _D = 12 A, | - | 28 | 66 | ns |
|---------------------|---------------------|---|---|----|-----|----|
| t _r | Turn-On Rise Time | $V_{GS} = 10 \text{ V}, R_{g} = 4.7 \Omega$ | - | 15 | 40 | ns |
| t _{d(off)} | Turn-Off Delay Time | | - | 73 | 156 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | - | 6 | 22 | ns |

Drain-Source Diode Characteristics

| I _S | Maximum Continuous Drain to Source Diode Forward Current | | | - | 24 | Α |
|-----------------|---|--|---|-----|-----|----|
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 72 | Α |
| V_{SD} | Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 12 A | | - | - | 1.2 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _{SD} = 12 A, | - | 123 | - | ns |
| Q _{rr} | Reverse Recovery Charge | $dI_F/dt = 100 A/\mu s$ | - | 597 | - | nC |

Notes:

- 1. Repetitive rating: pulse width limited by maximum junction temperature.
- 2. I_{AS} = 4.7 A, R_{G} = 25 Ω , Starting T_{J} = 25°C.
- 3. I $_{SD} \leq$ 12 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ 380 V, Starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

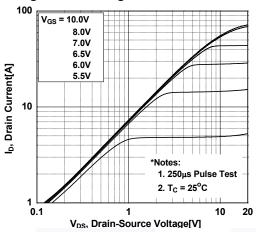


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

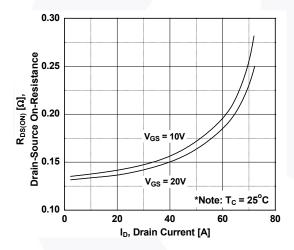


Figure 5. Capacitance Characteristics

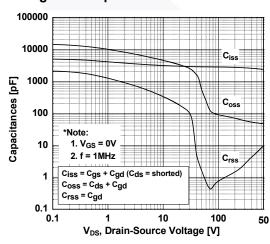


Figure 2. Transfer Characteristics

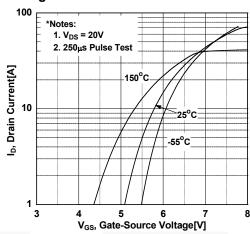


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

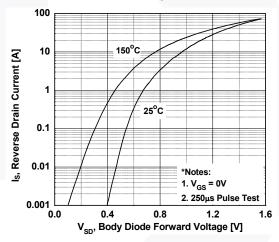
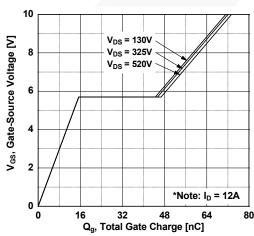


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

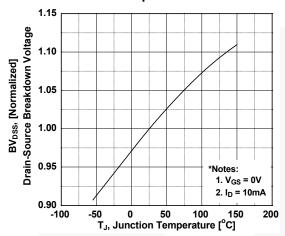


Figure 9. Maximum Safe Operating Area

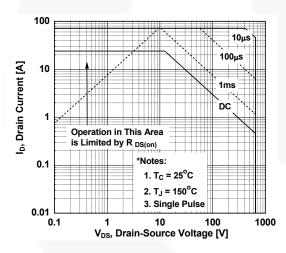


Figure 11. Eoss vs. Drain to Source Voltage

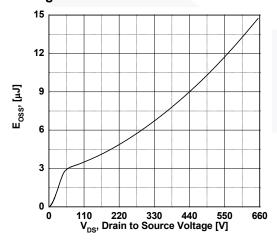


Figure 8. On-Resistance Variation vs. Temperature

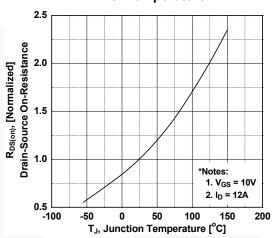
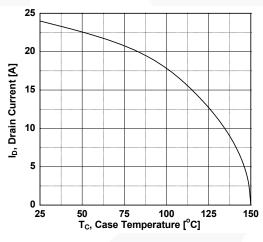
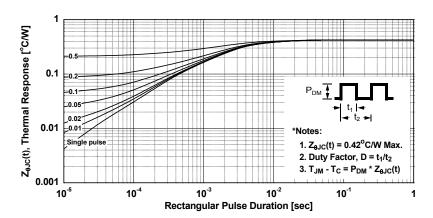


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



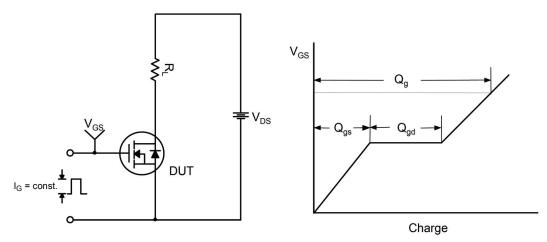


Figure 13. Gate Charge Test Circuit & Waveform

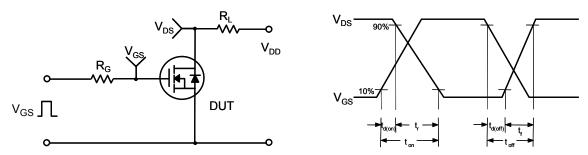


Figure 14. Resistive Switching Test Circuit & Waveforms

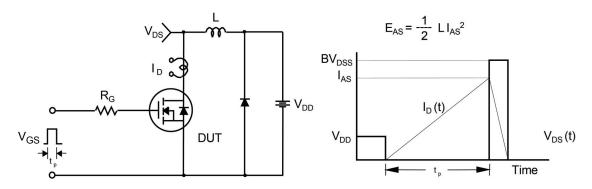
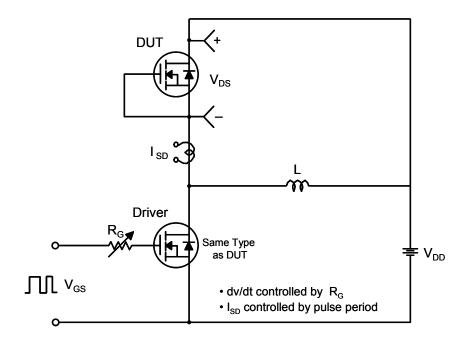


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms



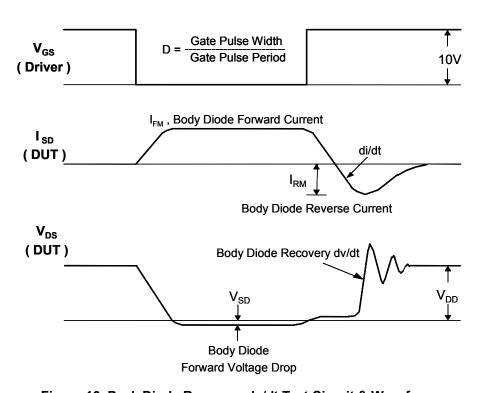


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

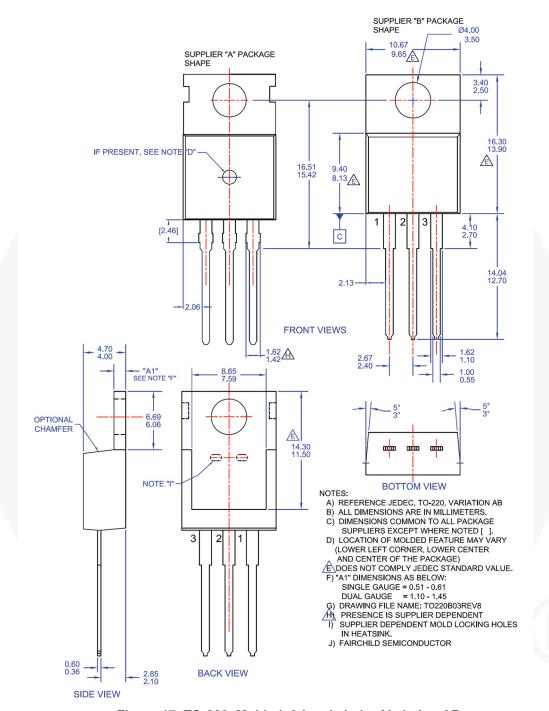


Figure 17. TO-220, Molded, 3-Lead, Jedec Variation AB

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